

EAST - [10726590.wsp:1]

File View Edit Tools Window Help

Drafts  
 Pending  
 Active  
 L1: (1069) trench and (ONO or oxide adj nitride adj oxide) and polysilicon and boron  
 L2: (3) trench near gate and (ONO or oxide adj nitride adj oxide) and (polysilicon with (dope\$1 n.  
 L3: (12) trench near gate and (ONO or oxide adj nitride adj oxide) and (polysilicon with (boron))  
 Failed  
 Saved  
 Favorites  
 Tagged (0)  
 UDC  
 Queue  
 Trash

Browse

Plurals

Default gpe Highlight all hit terms initially

trench near gate and (ONO or oxide adj nitride adj oxide) and (polysilicon with (boron))

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	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20030032249 A1	20030213	17	Semiconductor device and manufacturing method thereof	438/270	257/330; 257/E21.149;
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20030001225 A1	20030102	80	Semiconductor device and method of fabricating the same	257/499	257/E21.549; 257/E21.625;
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6784471 B2	20040831	16	Semiconductor device and manufacturing method thereof	257/288	257/235; 257/245;
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6624044 B2	20030923	28	Method for manufacturing semiconductor device having trench filled with polysilicon	438/425	257/E21.245; 257/E21.572;
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6580137 B2	20030617	33	Damascene double gated transistors and related manufacturing methods	257/401	257/407; 257/E21.409;
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6495863 B2	20021217	39	Semiconductor device having diode for input protection circuit of MOS structure	257/106	257/199; 257/481;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6180458 B1	20010130	13	Method of producing a memory cell configuration	438/259	257/E21.677; 257/E27.102;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 5821591 A	19981013	13	High density read only memory cell configuration and method for its production	257/390	257/329; 257/E27.102
11	<input type="checkbox"/>	<input type="checkbox"/>	US 4833094 A	19890523	15	Method of making a dynamic ram cell having shared trench storage capacitor	438/243	257/E21.166; 257/E21.651;
12	<input type="checkbox"/>	<input type="checkbox"/>	US 4785337 A	19881115	15	Dynamic ram cell having shared trench storage capacitor with sidewall-defined	257/304	257/382; 257/900;